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rfmd.com

STQ-1016(Z)

250MHZ TO 1000MHZ DIRECT OUADRATURE **MODULATOR**



RFMD Green, RoHS Compliant, Pb-Free (Z Part Number) Package: TSSOP, 16-Pin, 5.0mmx6.4mmx1.0mm

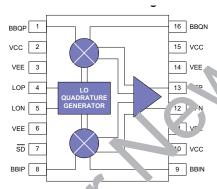
Product Description

RFMD's STQ-1016Z is a direct quadrature modulator targeted for use in a wide range of communications systems, including cellular/PCS, GSM, CDMA, TETRA, and ISM datacom. This device features a wide 250MHz to 1000MHz operating frequency band, excellent carrier and sideband suppression, and a low broadband noise floor.

The STQ-1016 uses silicon germanium (SiGe) device technology and delivers a typical output power of -9dBm with greater than 60dB IM3 suppression. A digital input shut-down feature is included that, when enabled, attenuates the output by 60dB. The device is packaged in an industry standard 16-pin TSSOP with exposed paddle for superb RF and thermal ground.

Optimum Technology Matching® Applied GaAs HBT GaAs MESFET InGaP HBT SiGe BiCMOS Si BiCMOS SiGe HBT GaAs pHEMT Si CMOS Si BJT GaN HFMT RF MEMS

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants.



Features

- Available in Lead Free, RoHS Compliant, and Green Packaging
- Excellent Carrier Feedthrough, -38dBm Constant Over Output Power
- Output 5 dB 5dBm
- Very Low Nowe Floor, -154 'Brny Hz Typical
- Maseband Input, DC to 5CCMHz
- Juperb Phase Accuracy and Amplitude Balance, ±0.5°C/±0.2dB
- Low LO Drive Requirement, -5dBm

Applications

- Cellular/PCS/GSM/CDMA Transceivers
- TETRA
- GMSK, QPSK, QAM, SSB Mod.

		- 1			
Parameter	Min.	S _F achication Typ.	Max.	Unit	Condition
RF Output: TA=25°C					
RF Frequency Range	50		1000	MHz	
Output Power	-1.	-9	-7	dBm	(Baseband input level 600 mV _{P-P} differential)
RF Port Return Loss		>10, 250 to 1000MHz >15, 275 to 500MHz		dB	Matched to 50Ω using schematic shown on page 5
Output P1dB	+3	+6		dBm	(Baseband input level 3.8V _{P-P} differential typical)
Carrier Feedthrough		-38	-30	dBm	
Sideband Suppress, n	34	42		dB	
IM3 Suppression	58	62		dB	2-tone BB input @ 600 mV _{P.P} diff. per tone, 20 kHz spacing
Broadband Noise Floor		-154	-150*	dBm/Hz	Baseband inputs tied to 1.9V _{DC} , -20 MHz offset from carrier
Quadrature Phase Error	-2.0	±0.5	+2.0	°C	
I/Q Amplitude Balance	-0.20	±0.05	+0.20	dB	
Supply Voltage	+4.75	+5.00	+5.25	V	
Supply Current		80	86	mA	
Device Thermal Resistance		25		°C/W	Junction to case

Test Conditions: V_{CE}=2.7V, I_O=11mA Typ. (unless otherwise noted), T_L=25°C. OIP3 Tone Spacing=1MHz, P_{OUT} per tone=-5dBm. [1] Data with Application Circuit.

STQ-1016(Z)



Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage (V _{CC})	6.0	V _{DC}
LO, RF Input (LOP, LON, RFP, RFN)	+10	dBm
Baseband Min Input Voltage (BBIP, BBIN, BBQP BBQN)	0	V _{DC}
Baseband Max Input Voltage (BBIP, BBIN, BBQP, BBQN)	3	V _{DC}
Operating Temperature	-40 to +85	°C
Storage Temperature	-65 to +150	°C

*Note: Load condition1, Z_L=50Ω. Load condition2, Z_L=10:1 VSWR.

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

 $I_DV_D < (T_J - T_L) / R_{TH}$, j-I and $T_L = \mathring{T}_{LEAD}$



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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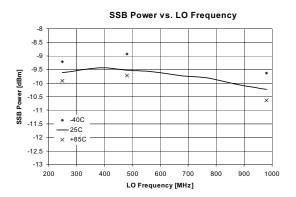
Parameter	Specification			Unit	Condition
Falailletei	Min.	Тур.	Max.	Oilit	Condition
Baseband Modulation Input:					
T _A =25°C					
Baseband Frequency Input	DC		500	MHz	3dB bandwidth, baseband inputs terminated in 50Ω
Baseband Input Resistance		4.4		kΩ	Per pin
Baseband Input Capacitance		0.5		F	Per pin
LO Input: T _A =25°C					
LO Frequency	250		1)00	MHz	
LO Drive Level	-8	-5		dBm	
LO Port Return Loss		>10, 250 to 1000 >15, 275 to 100	3	MHz	Matched to 50Ω using schematic shown on page 5
Miscellaneous: T _A =25°C					
Shut-Down Supply Current		, t5	60	mA	Shut-down enabled
Shut-Down Attenuation		2		dB	
Shut-Down Pin Resistance		11.5		kΩ	@ 1MHz
Shut-Down Pin Capacitance		.2		pF	@ 1MHz
Shut-Down Control Voltage Thresholds	,.75		V _{CC}	V	Shut-Down disabled (normal operation)
	0.0		1.5	V	Shut-Down enabled
Shut-Down Settling Time		<450		ns	

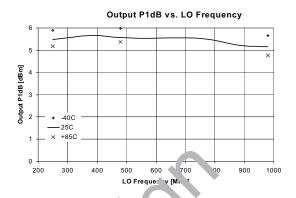
Test Conditions (for all product specific, tion tables unless otherwise noted): V_{CC} (pins 2, 10, 15)=+5V, T_A =+25°C, Baseband Input (Pins 1, 8, 9, 16° \pm 2V \pm 3° ias, 200 kHz frequency, 300 mV_{P-P} per pin=600 mV_{P-P} differential drive, I and Q signals in quadrature, LO

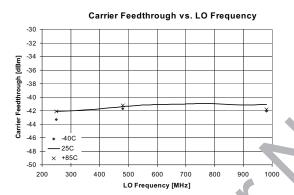
Input (Pins 4, 5) = -5 dBm @ 25(to 10c)MHz

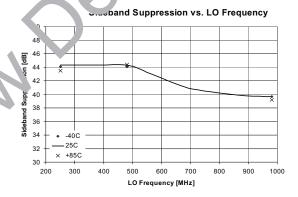


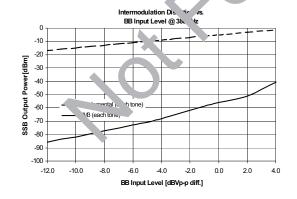
250 MHz to 1000 MHz Typical Device Performance

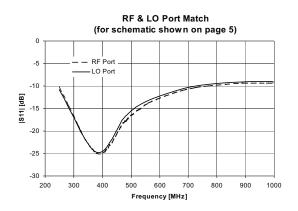










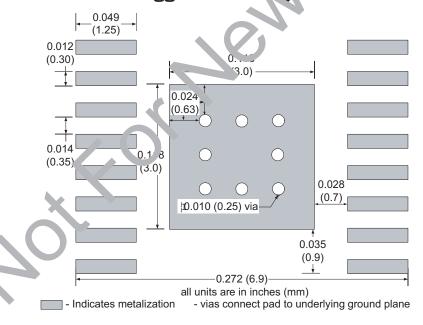


STQ-1016(Z)



Pin	Function	Description				
1	BBQP	Q-channel baseband input, positive terminal. Nominal DC bias voltage is 1.9V (biased internally).				
2	VCC	Positive supply (+5V).				
3	VEE	Ground.				
4	LOP	Local oscillator input, positive terminal. Nominal DC voltage is 2.0V. Input should be AC-coupled.				
5	LON	Local osicillator input, negative terminal. Nominal DC voltage is 2.0. Input should be AC-coupled.				
6	VEE	Ground.				
7	SD	Shut-down control. Logic high=normal operation; logic low=shut-down enabled.				
8	BBIP	I-channel baseband input, positive terminal. Nominal DC bias voltage is 1.9V (biased internally).				
9	BBIN	I-channel baseband input, negative terminal. Nominal DC bias voltage is 1.9V (biased internal).				
10	VCC	Positive supply (+5V).				
11	VEE	Ground.				
12	RFN	RF output, negative terminal. Nominal DC voltage is 2.4V. Output should be AC-coupled				
13	RFP	RF output, positive terminal. Nominal DC voltage is 2.4V. Output should be AC				
14	VEE	Ground.				
15	VCC	Positive supply (+5V).				
16	BBQN	Q-channel baseband input, negative terminal. Nominal DC b. s voltage 1.9V (biased internally).				

Suggested Pad 'ayout

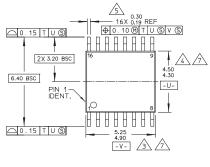


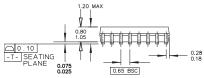


Package Drawing

Dimensions in inches (millimeters)

Refer to drawing posted at www.rfmd.com for tolerances.





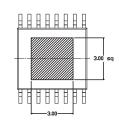


- NOTES:

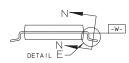
 1. CONTROLLING DIMENSION: MILLIMETER
 - DIMENSIONS AND TOLERANCES PER ANSI Y14.5M-1982.

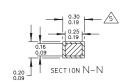
- 2 DIMENSIONS AND TOLERANCES PER ANSI Y14.5M-1992.

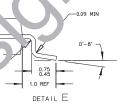
 3 DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SMALL NOT EXCEED 0.15 PER SIGN DIMENSION DIMENSI
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSIONS ARE TO BE DETERMINED AT DATUM PLANE -W-



BOTTOM VIEW



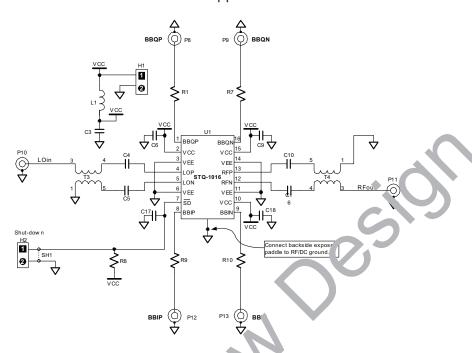




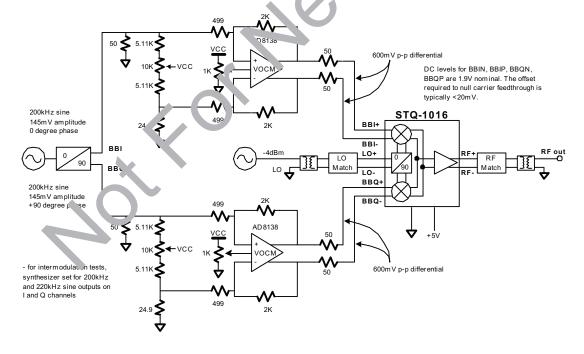


Application Schematic

250 MHz to 1000 MHz Application Schematic



Direct Quadrature Modulator: Seneral Test Set-Up





Bill of Materials (for 250 MHz to 1000 MHz Evaluation Board P/N STQ-1016EVB)

Component	Value	Qty	Vendor	Part Number	Description
Designator					
U1		1	SMDI	STQ-1016	SiGe Direct Quadrature Modulator
P8, P9, P10, P11, P12, P13		6	Johnson Compo- nents	142-0701-851	SMA connector, end launch with tab, for 0.062" thick board
H1, H2		2	AMP	640453-2	2-pin header, right angle
T3, T4	1:1	2	M/A COM	ETC1-1-13	RF transformer, 4.5 MHz to 3000 MHz
L1	1uH	1	Panasonic	ELJ-FA1R0KF2	Inductor, 1210 footprint, ±10% tolerance
R1, R7, R9, R10	200Ω	4	Venkel	CR1206-8W-2000T	Resistor, 1206 footprint, ±1% tolerance
R8	1kΩ	1	Venkel	CR0603-16W-1001FT	Resistor, 0603 footprint +1% tolerance
C6, C18	33 pF	2	Venkel	C0603C0G500- 330JNE	Capacitor, 0603 footprint, COC diele 'ric, ±5% tolerance
C9, C17	1nF	2	Venkel	C0603C0G500- 102JNE	Capacitor, 0603 footpri t, CC ? dic ectric, ±5% tolerance
C3	2.2uF	1	Venkel	C1206Y5V160- 225ZNE	Capacitor, 1206 to tpr. SV ielectric, 16V rating
C4, C5, C10, C16	22pF	4	Venkel	C0603C0G500- 220JNE	Capacitor, 06 3 July int, COG dielectric, ±5% tolerance
SH1		1	ЗМ	929950-00	Shunt for 2-pin header

Ordering Information

Part Number	Reel Size	Devices/Reel		
STQ-1016(Z)	7"	1000		



